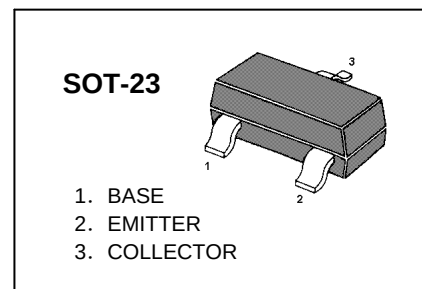


TRANSISTOR (NPN)

FEATURE

Power dissipation



MARKING : HF

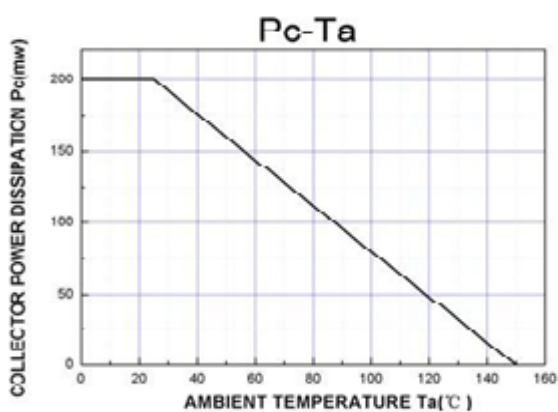
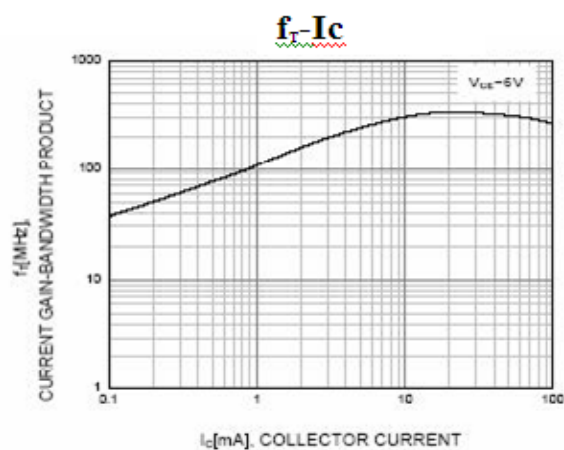
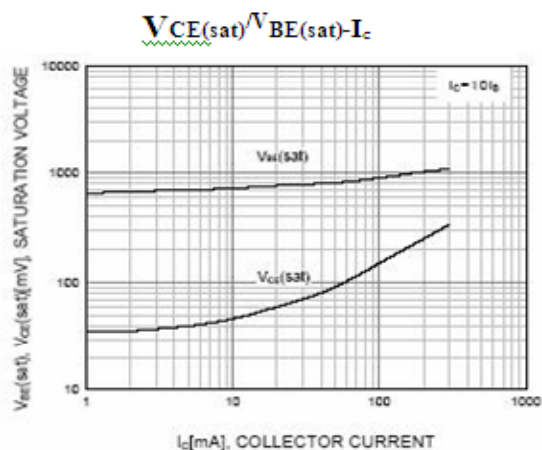
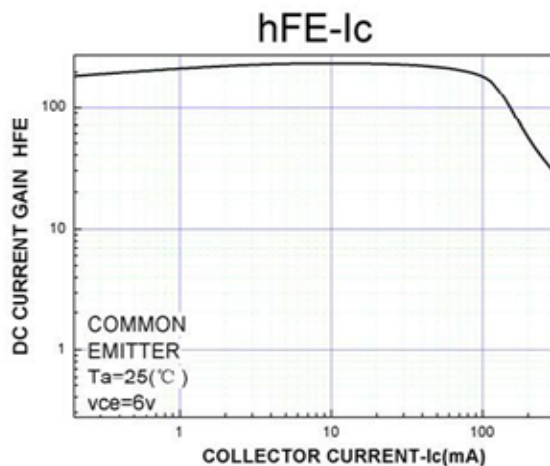
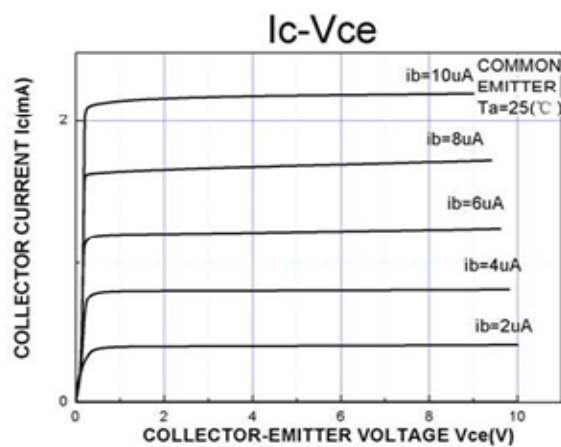
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	50	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	150	mA
P_C	Collector Power Dissipation	200	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55-150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=0.1\text{mA}$, $I_B=0$	50			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}$, $I_E=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=50\text{V}$, $I_B=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=6\text{V}$, $I_C=2\text{mA}$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			0.25	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=100\text{mA}$, $I_B=10\text{mA}$			1	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=1\text{mA}$, $f=30\text{MHz}$	80			MHz

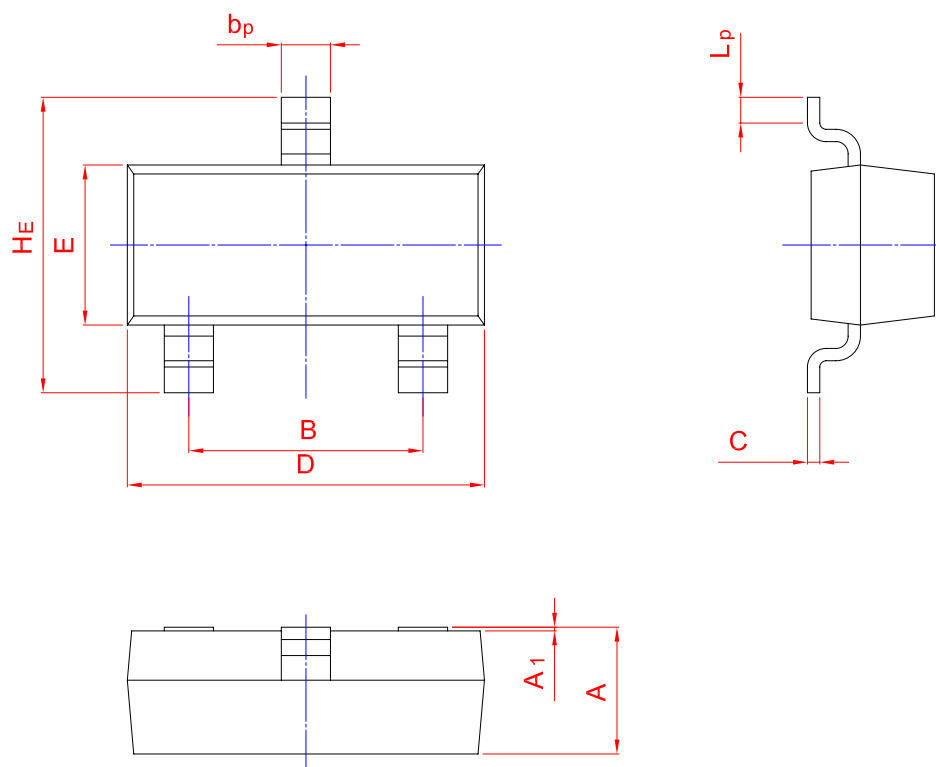
Typical Characteristics



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-23



UNIT	A	B	b_p	C	D	E	H_E	A_1	L_p
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20